In the Claims:

1. -25. Cancelled

26. (Currently Amended) A method of forming a semiconductor device, the method comprising:

providing a substrate;

forming a first interlayer dielectric on the substrate;

forming a ~~connection node~~ capacitor contact pad located in the first interlayer dielectric in a first region;

forming a second interlayer dielectric on the first interlayer dielectric;

forming an integrated capacitor having a first top electrode and a first bottom electrode formed in the second interlayer dielectric such that the first bottom electrode is in electrical contact with the ~~connection node~~ capacitor contact pad, at least a portion of the integrated capacitor being positioned over the capacitor contact pad; and

forming a ~~connection node~~ capacitor contact pad contact through the second interlayer dielectric providing an electrical connection to the ~~connection node~~ capacitor contact pad, the capacitor contact pad contact being positioned over the capacitor contact pad.

27. (Original) The method of claim 26, further comprising forming a device on a second region of the substrate before forming the first interlayer dielectric.

28. (Original) The method of claim 27, wherein the device is a transistor.

29. (Currently Amended) The method of claim 28, further comprising simultaneously forming a contact in the first interlayer dielectric when the step of forming a ~~connection node~~ capacitor contact pad is performed, wherein the contact is electrically connected to the transistor.

30. (Original) The method of claim 29, further comprising simultaneously forming a storage capacitor in the second interlayer dielectric when the step of forming the integrated capacitor is performed, wherein the storage capacitor has a second top electrode and a second bottom electrode formed such that the second bottom electrode is in electrical contact with the transistor via the contact.

31. (Currently Amended) The method of claim 29, wherein the ~~connection node~~ capacitor contact pad and the contact are formed of a first material.

32. (Original) The method of claim 31, wherein the first material is a material selected from the group consisting of a metal, an elemental metal, a transition metal, and a combination thereof.

33. -35. Cancelled

36. (Currently Amended) A method of forming a semiconductor device, the method comprising:

providing a substrate having at least one first region and one second region;

forming a transistor on the first region;

forming a first interlayer dielectric over the substrate;

forming a ~~connection node~~ capacitor contact pad in the first interlayer dielectric upon the

second region, the ~~connection node~~ capacitor contact pad being a thickness substantially equivalent to the thickness of the first interlayer dielectric;

forming a second interlayer dielectric on the first interlayer dielectric;

forming an integrated capacitor in the second interlayer dielectric upon the second region and a storage capacitor in the second interlayer dielectric upon the first region, the integrated capacitor having a first bottom electrode being in electrical contact with the ~~connection node~~ capacitor contact pad and the storage capacitor having a second bottom electrode , the second bottom electrode being in electrical contact with the transistor, at least a portion of the integrated capacitor is positioned over the capacitor contact pad; and

forming a ~~connection node~~ capacitor contact pad contact in the second dielectric layer, the ~~connection node~~ capacitor contact pad contact being in electrical contact with the ~~connection node~~ capacitor contact pad and positioned over the capacitor contact pad.

37. (Currently Amended) The method of claim 36, further comprising simultaneously forming a transistor contact in the first interlayer dielectric when the step of forming the ~~connection node~~ capacitor contact pad is performed, wherein the transistor contact electrically connects a source/drain of the transistor with the second bottom electrode.

38. (Currently Amended) The method of claim 37, wherein the transistor contact and the ~~connection node~~ capacitor contact pad are formed of a first material.

39. (Original) The method of claim 38, wherein the first material is a material selected from the group consisting of a metal, an elemental metal, a transition metal, and a combination thereof.

40. (Currently Amended) The method of claim 36, wherein the ~~connection node~~ capacitor contact pad is formed of a material selected from the group consisting of a metal, an elemental metal, a transition metal, and a combination thereof.

41. (Currently Amended) The method of claim 36, wherein forming the ~~connection node~~ capacitor contact pad includes forming a barrier layer on the first interlayer dielectric and forming a conductive layer on the barrier layer.

42. (Original) The method of claim 41, wherein the barrier layer is formed of a material selected from the group consisting of titanium, titanium nitride, and combinations thereof.

43. (Original) The method of claim 41, wherein the conductive layer comprises tungsten.

44. -57. Cancelled